

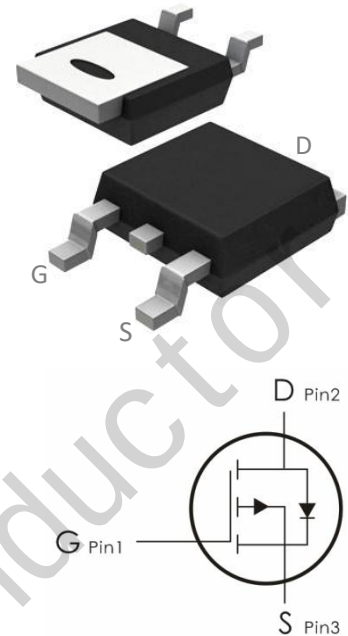
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-60V, I_D=-20A, R_{DS(on)} < 68m\ \Omega @ V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C^1$	-20	A
	Continuous Drain Current- $T_C=100^\circ C^1$	-11	A
I_{DM}	Pulsed Drain Current ²	-36	A
E_{AS}	Single Pulse Avalanche Energy ³	35.4	mJ
I_{AS}	Avalanche Current	-26.6	A
P_D	Total Power Dissipation- $T_C=25^\circ C^4$	34.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance Junction to Case ¹	3 6	°C/W
$R_{\theta JA}$	Thermal Resistance- Junction to Ambient ¹	62	°C/W

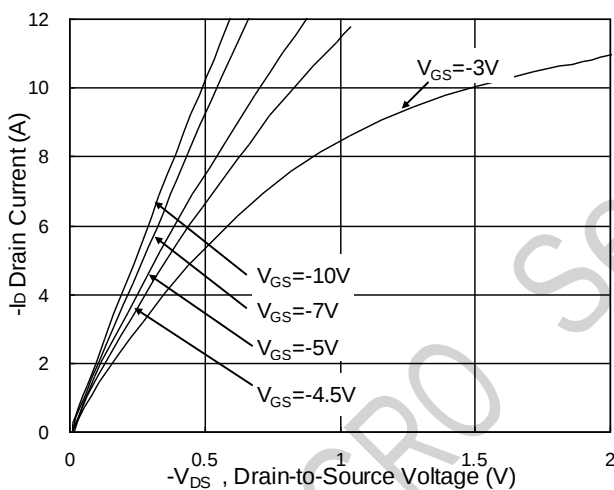
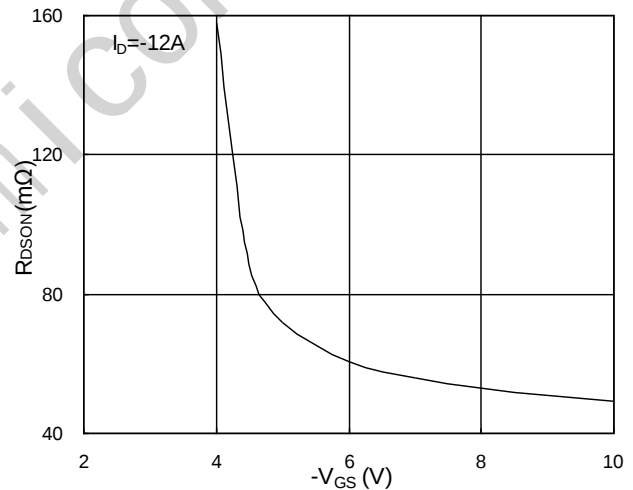
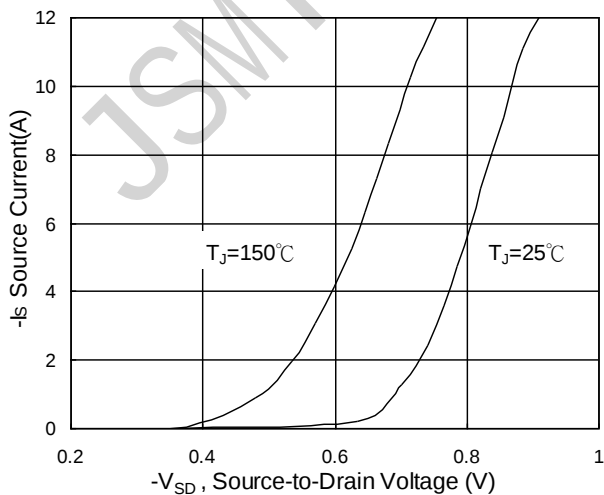
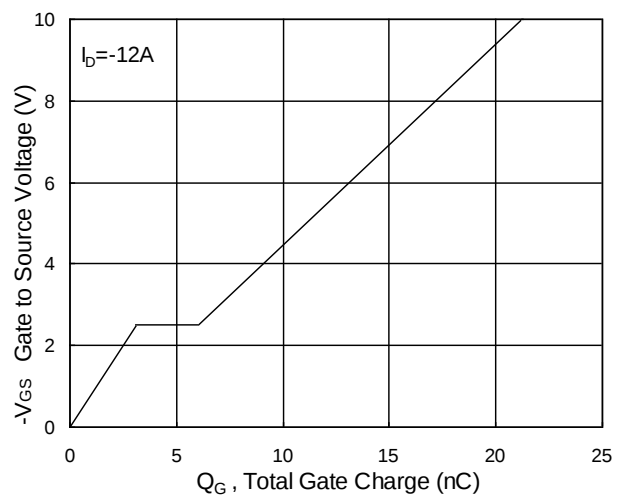
Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

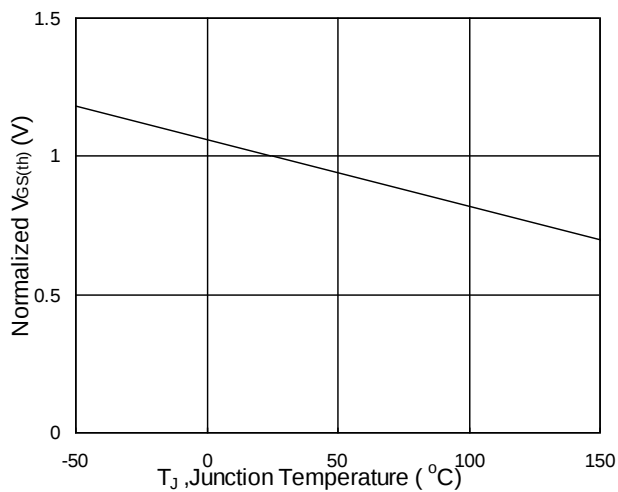
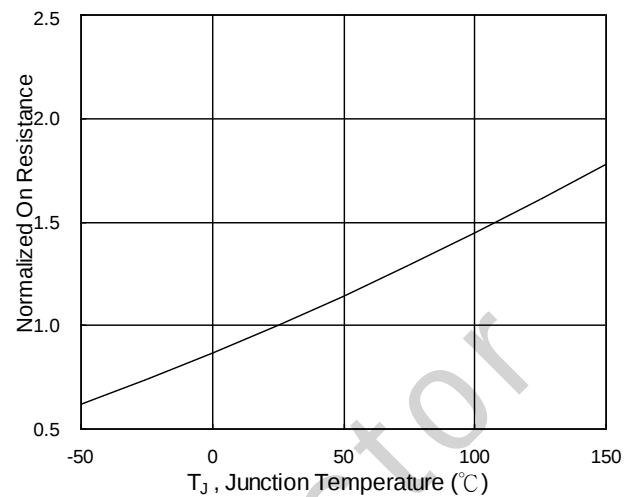
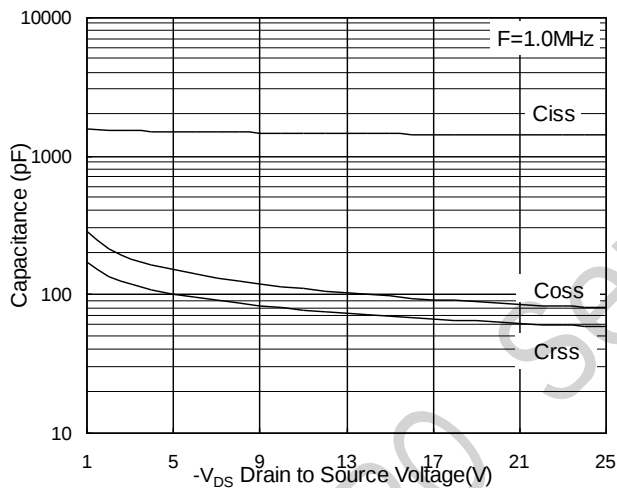
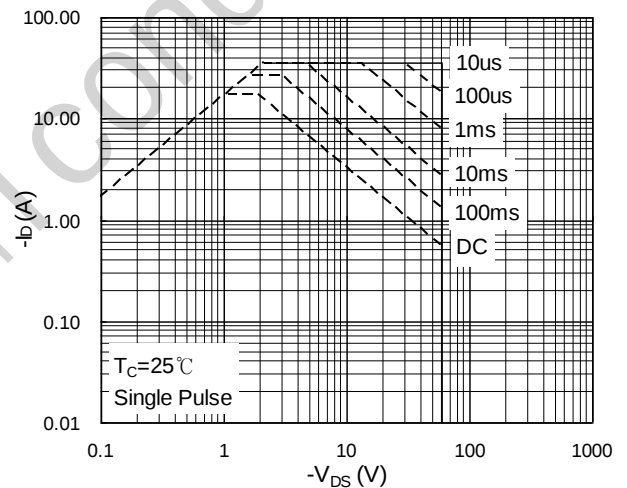
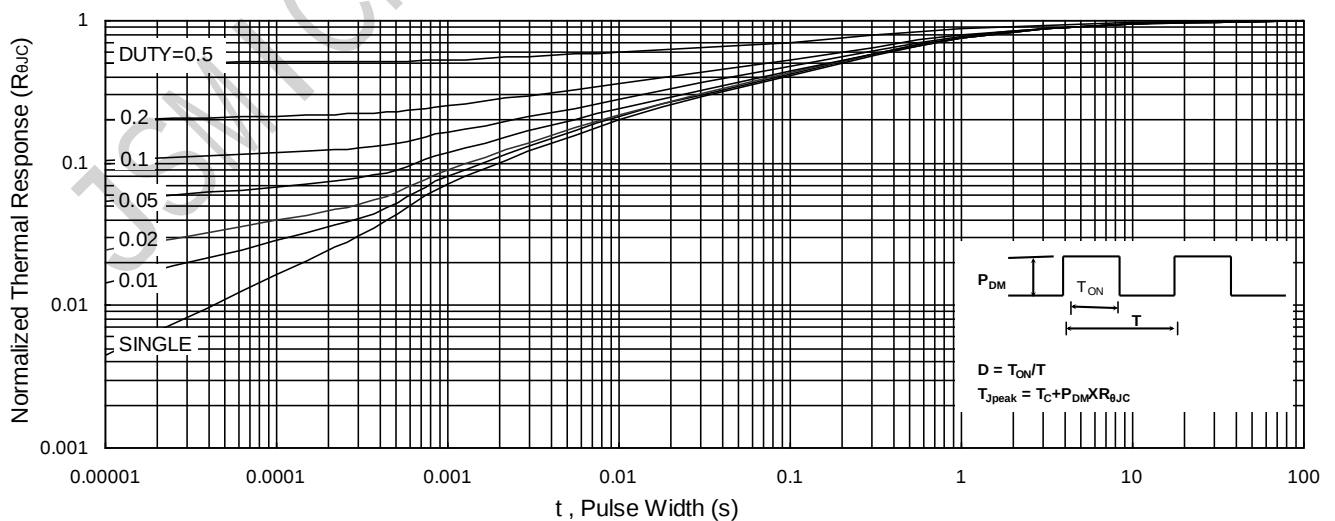
Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-60	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-48V, T _J =25 °C	---	---	1	μ A
		V _{GS} =0V, V _{DS} =-48V, T _J =55 °C	---	---	5	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1.2	---	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ²	V _{GS} =-10V, I _D =-12A	---	---	68	m Ω
		V _{GS} =-4.5V, I _D =-8A	---	---	105	m Ω
G _{FS}	Forward Transconductance	V _{DS} =-5V , I _D =-12A	---	15.4	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1440	---	pF
C _{oss}	Output Capacitance		---	97	---	
C _{rss}	Reverse Transfer Capacitance		---	65	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _G =3.3 Ω	---	28.8	---	ns
t _r	Rise Time		---	19.8	---	ns
t _{d(off)}	Turn-Off Delay Time		---	60.8	---	ns
t _f	Fall Time		---	7.2	---	ns
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-48V,	---	9.86	---	nC
Q _{gs}	Gate-Source Charge	I _D =-10A	---	3.08	---	nC

Q_{gd}	Gate-Drain "Miller" Charge		---	2.95	---	nC
R_G	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	13.5	---	Ω
Drain-Source Diode Characteristics						
V_{SD}	Drain Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
I_S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-18	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-36	A

Notes:

- 1.The data tested by surface mounted on a 1 inch FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-26.6A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics: (T_C=25°C unless otherwise noted)

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance v.s Gate-Source

Fig.3 Forward Characteristics of Reverse

Fig.4 Gate-Charge Characteristics


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

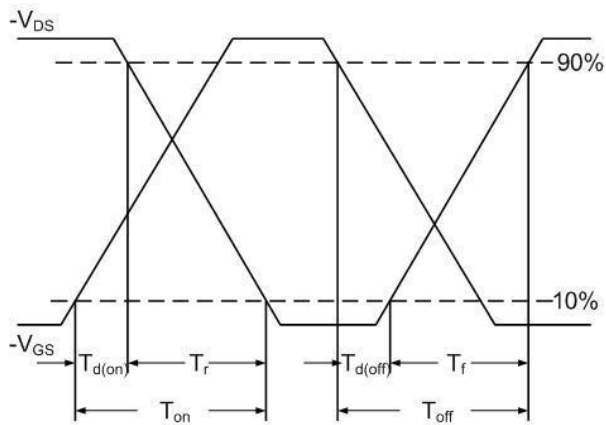


Fig.10 Switching Time Waveform

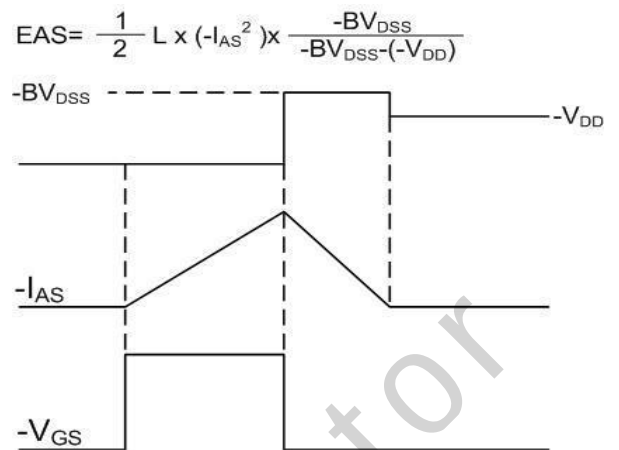


Fig.11 Unclamped Inductive Waveform

外形尺寸图 / Package Dimensions

